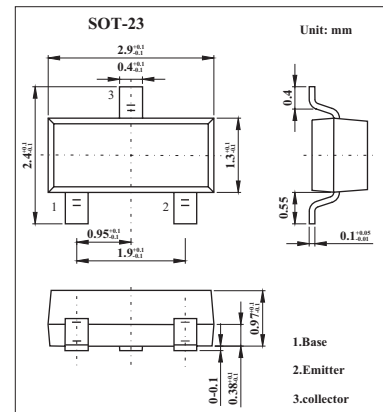


## Silicon PNP Epitaxia

## 2SA1365

## ■ Features

- Low collector to emitter saturation voltage.
- Excellent linearity of DC forward current gain.
- Super mini package for easy mounting.
- High collector current.
- High gain band width product.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	-25	V
Collector-emitter voltage	$V_{CE0}$	-20	V
Emitter-base voltage	$V_{EB0}$	-4	V
Peak collector current	$I_{CM}$	-1	A
Collector current	$I_C$	-700	mA
Collector dissipation ( $T_a=25^\circ\text{C}$ )	$P_C$	150	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10 \mu\text{A}, I_E = 0$	-25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -100 \mu\text{A}, R_{BE} = \infty$	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10 \mu\text{A}, I_C = 0$	-4			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -25 \text{ V}, I_E = 0$			-1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -2 \text{ V}, I_C = 0$			-1	$\mu\text{A}$
DC current gain ( * )	$h_{FE}$	$V_{CE} = -4 \text{ V}, I_C = -100 \text{ mA}$	150		800	
Collector-emitter saturation voltage	$V_{CE}$	$I_C = -500 \text{ mA}, I_B = -25 \text{ mA}$		-0.2	-0.5	V
Gain band width product	$f_T$	$V_{CE} = -6 \text{ V}, I_E = 10 \text{ mA}$		180		MHz

\* It shows  $h_{FE}$  classification in right table.

■  $h_{FE}$  Classification

Marking	AE	AF	AG
$h_{FE}$	150~300	250~500	400~800